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## EDITORIAL

A Warm Welcome to Two New T-ED Editors ..... *J. D. Cressler* 935

## REGULAR PAPERS

### Silicon and Column IV Semiconductors Devices

Profiling of Channel-Hot-Carrier Stress-Induced Trap Distributions Along Channel and Gate Dielectric in High- $k$ Gated MOSFETs by a Modified Charge Pumping Technique .....	<i>C.-C. Lu, K.-S. Chang-Liao, C.-H. Tsao, T.-K. Wang, H.-C. Ko, and Y.-T. Hsu</i>	936
Studies of Safe Operating Area of InGaP/GaAs Heterojunction Bipolar Transistors .....	<i>C.-P. Lee, N. G. M. Tao, and B. J.-F. Lin</i>	943
Experimental Investigation on Alloy Scattering in sSi/Si <sub>0.5</sub> Ge <sub>0.5</sub> /sSOI Quantum-Well p-MOSFET .....	<i>W. Yu, W. Wu, B. Zhang, C. Liu, J. Sun, D. Zhai, Y. Yu, X. Wang, Y. Shi, Y. Zhao, and Q.-T. Zhao</i>	950
Top-Down Fabrication of Epitaxial SiGe/Si Multi-(Core/Shell) p-FET Nanowire Transistors .....	<i>S. Barraud, J.-M. Hartmann, V. Maffini-Alvaro, L. Tosti, V. Delaye, and D. Lafond</i>	953
Modeling Quasi-Static Characteristics of Devices Consisting of Silicon, Dielectrics, and Conductors Based on Their Helmholtz Free Energy .....	<i>M. A. Sattar, N. Gunther, and M. Rahman</i>	957
Stack Gate Technique for Dopingless Bulk FinFETs .....	<i>Y.-B. Liao, M.-H. Chiang, Y.-S. Lai, and W.-C. Hsu</i>	963
Analytical Modeling of Threshold Voltage and Interface Ideality Factor of Nanoscale Ultrathin Body and Buried Oxide SOI MOSFETs With Back Gate Control .....	<i>N. Fasarakis, T. Karatsori, D. H. Tassis, C. G. Theodorou, F. Andrieu, O. Faynot, G. Ghibaudo, and C. A. Dimitriadis</i>	969
A Conjoined Electron and Thermal Transport Study of Thermal Degradation Induced During Normal Operation of Multigate Transistors .....	<i>M. Mohamed, Z. Aksamija, W. Vitale, F. Hassan, K.-H. Park, and U. Ravaioli</i>	976
Accuracy of Microwave Transistor $f_T$ and $f_{MAX}$ Extractions .....	<i>V. Teppati, S. Tirelli, R. Lövlom, R. Flückiger, M. Alexandrova, and C. R. Bolognesi</i>	984

(Contents Continued on Page 933)



Investigation of Key Technologies for Poly-Si/TaN/HfLaON/IL SiO <sub>2</sub> Gate-Stacks in Advanced Device Applications .....	<i>Q. Xu, G. Xu, Y. Li, H. Zhou, J. Li, J. Niu, M. Ding, D. Chen, and T. Ye</i>	991
Analysis of Harmonic Distortion in UDG-MOSFETs .....	<i>A. Dutta, K. Koley, S. K. Saha, and C. K. Sarkar</i>	998
<b>Compound Semiconductor Devices</b>		
A Thickness-Mode AlGaN/GaN Resonant Body High Electron Mobility Transistor ....	<i>A. Ansari and M. Rais-Zadeh</i>	1006
Modeling of the Gate Leakage Current in AlGaN/GaN HFETs .....	<i>A. Goswami, R. J. Trew, and G. L. Bilbro</i>	1014
Comprehensive Study of the Complex Dynamics of Forward Bias-Induced Threshold Voltage Drifts in GaN Based MIS-HEMTs by Stress/Recovery Experiments .....	<i>P. Lager, M. Reiner, D. Pogany, and C. Ostermaier</i>	1022
Fast Analytical Modeling of Dynamic Thermal Behavior of Semiconductor Devices and Circuits .....	<i>K. H. Kwok and V. d'Alessandro</i>	1031
Toward Conformal Damage-Free Doping With Abrupt Ultrashallow Junction: Formation of Si Monolayers and Laser Anneal as a Novel Doping Technique for InGaAs nMOSFETs .....	<i>E. Y.-J. Kong, P. Guo, X. Gong, B. Liu, and Y.-C. Yeo</i>	1039
Optimal AlGaN/GaN HEMT Buffer Layer Thickness in the Presence of an Embedded Thermal Boundary .....	<i>D. I. Babić</i>	1047
<b>Memory Devices and Technology</b>		
Memristor: Part I—The Underlying Physics and Conduction Mechanism .....	<i>A. Mazady and M. Anwar</i>	1054
Memristor: Part II—DC, Transient, and RF Analysis .....	<i>A. Mazady and M. Anwar</i>	1062
Characteristic Evolution from Rectifier Schottky Diode to Resistive-Switching Memory With Al-Doped Zinc Tin Oxide Film .....	<i>Y.-S. Fan and P.-T. Liu</i>	1071
<b>Thin Film Transistors</b>		
The Resistivity of Zinc Oxide Under Different Annealing Configurations and Its Impact on the Leakage Characteristics of Zinc Oxide Thin-Film Transistors .....	<i>L. Lu and M. Wong</i>	1077
Influence of Mechanical Bending on Flexible InGaZnO-Based Ferroelectric Memory TFTs .....	<i>L. Petti, N. Münzenrieder, G. A. Salvatore, C. Zysset, T. Kinkeldei, L. Büthe, and G. Tröster</i>	1085
<b>Optoelectronics, Displays, and Imaging</b>		
Electrically Stable, Solution-Processed Amorphous Oxide IZO Thin-Film Transistors Through a UV-Ozone Assisted Sol-Gel Approach .....	<i>T. B. Singh, J. J. Jasieniak, L. de Oliveira Tozi, C. D. Easton, and M. Bown</i>	1093
Current Components and Their Temperature Dependence of Green and Blue Light-Emitting Diodes: A Quantitative Comparison .....	<i>D.-W. Kim, Y.-C. Lee, J.-O. Ryu, and S.-B. Kim</i>	1101
Electrical Instability of Double-Gate a-IGZO TFTs With Metal Source/Drain Recessed Electrodes .....	<i>G. Baek, L. Bie, K. Abe, H. Kumomi, and J. Kanicki</i>	1109
<b>Solid-State Power and High Voltage Devices</b>		
Fast 3-D Electrothermal Device/Circuit Simulation of Power Superjunction MOSFET Based on SDevice and HSPICE Interaction .....	<i>A. Chvála, D. Donoval, J. Marek, P. Příbytný, M. Molnár, and M. Mikolášek</i>	1116
<b>Materials, Processing and Packaging</b>		
Design Metrics Improvement for SRAMs Using Symmetric Dual- <i>k</i> Spacer (SymD- <i>k</i> ) FinFETs .....	<i>P. K. Pal, B. K. Kaushik, and S. Dasgupta</i>	1123
Low-Temperature Bonded Cu/In Interconnect With High Thermal Stability for 3-D Integration .....	<i>Y.-S. Chien, Y.-P. Huang, R.-N. Tzeng, M.-S. Shy, T.-H. Lin, K.-H. Chen, C.-T. Chiu, C.-T. Chuang, W. Hwang, J.-C. Chiou, H.-M. Tong, and K.-N. Chen</i>	1131
<b>Solid State Device Phenomena</b>		
Heat Dissipation in Resistive Switching Devices: Comparison of Thermal Simulations and Experimental Results ....	<i>E. Yalon, I. Riess, and D. Ritter</i>	1137
Numerical Study of Very Small Floating Islands .....	<i>H. Watanabe, K. (C.-W.) Yao, and J. (P.-J.) Lin</i>	1145
New Models for Impact Ionization in Submicrometer Devices .....	<i>Q. Chau</i>	1153
Low-Frequency Noise Sources in Advanced UTBB FD-SOI MOSFETs .....	<i>C. G. Theodorou, E. G. Ioannidis, F. Andrieu, T. Poiroux, O. Faynot, C. A. Dimitriadis, and G. Ghibaudo</i>	1161
<b>Molecular and Organic Devices</b>		
Current Noise and AC Response of a Back-Gated Single-Molecule Junction ....	<i>W.-H. Zhu, G.-H. Ding, and B. Dong</i>	1168
All-Solution-Processed Low-Voltage Organic Thin-Film Transistor Inverter on Plastic Substrate .....	<i>L. Feng, W. Tang, J. Zhao, Q. Cui, C. Jiang, and X. Guo</i>	1175

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**Vacuum Electron Devices**

Numerical Computation of Dispersion Curves in Arbitrary Cylindrical Metal SWSs Without Approximating the Boundary Shape With Fourier Series Expansion .....	<i>D. Zhang, J. Zhang, H.-H. Zhong, and Z.-X. Jin</i>	1181
Monotron Oscillation in Double-Gap Coupling Output Cavities of Multiple-Beam Klystrons .....	<i>F.-M. Lin and X.-P. Li</i>	1186

**Emerging Technologies and Devices**

Performance Analysis of Graphene Nanoribbon Field Effect Transistors in the Presence of Surface Roughness .....	<i>M. Sanaeepur, A. Y. Goharrizi, and M. J. Sharifi</i>	1193
A Comprehensive Graphene FET Model for Circuit Design .....	<i>S. Rodriguez, S. Vaziri, A. Smith, S. Frégonèse, M. Ostling, M. C. Lemme, and A. Rusu</i>	1199

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BRIEF PAPERS

Complementary Magnetic Tunnel Junction Logic .....	<i>J. S. Friedman and A. V. Sahakian</i>	1207
Simulation and Investigation of Random Grain-Boundary-Induced Variabilities for Stackable NAND Flash Using 3-D Voronoi Grain Patterns .....	<i>C.-W. Yang and P. Su</i>	1211

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